

ABSTRACT

A plasma processing apparatus of the present invention can reduce a manufacturing cost of the apparatus and a footprint by decreasing a load applied to a device for
5 varying a distance between electrodes in comparison with a conventional apparatus and, at the same time, easily meet a scaling up of a substrate to be processed. A lower electrode and an upper electrode are installed inside a
10 vacuum chamber. Provided at a lower electrode supporting member are openings for operating the upper electrode by using a driving mechanism installed outside the vacuum chamber. An intermediate ring is installed at bellows for air-tightly sealing the openings. Further, the intermediate
15 ring is connected to a connecting member connected to an upper electrode supporting member and the driving mechanism.